

SOT-23 Plastic-Encapsulate Transistors

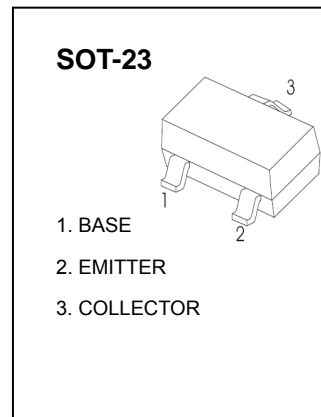
KSA1182 TRANSISTOR (PNP)

FEATURES

Complement to KSC2859

MAXIMUM RATINGS (T_a=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V _{CBO}	Collector-Base Voltage	-35	V
V _{CEO}	Collector-Emitter Voltage	-30	V
V _{EBO}	Emitter-Base Voltage	-5	V
I _C	Collector Current -Continuous	-0.5	A
P _C	Collector Power Dissipation	150	mW
T _j	Junction Temperature	150	°C
T _{stg}	Storage Temperature	-55-150	°C



ELECTRICAL CHARACTERISTICS (T_a=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C =-100μA, I _E =0	-35			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C =-1mA, I _B =0	-30			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E =-100μA, I _C =0	-5			V
Collector cut-off current	I _{CBO}	V _{CB} =-35V, I _E =0			-0.1	μA
Emitter cut-off current	I _{EBO}	V _{EB} =-5V, I _C =0			-0.1	μA
DC current gain	h _{FE(1)}	V _{CE} =-1V, I _C =-100mA	70		240	
	h _{FE(2)}	V _{CE} =-6V, I _C =-400mA	25			
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =-100mA, I _B =-10mA			-0.25	V
Base-emitter voltage	V _{BE}	V _{CE} =-1V, I _C =-100mA			-1.0	V
Transition frequency	f _T	V _{CE} =-6V, I _C =-20mA		200		MHz
Collector output capacitance	C _{ob}	V _{CB} =-6V, I _E =0, f=1MHz		13		pF

CLASSIFICATION OF h_{FE(1)}

Rank	O	Y
Range	70-140	120-240
Marking	F1O	F1Y